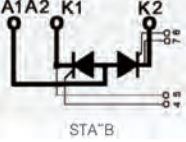
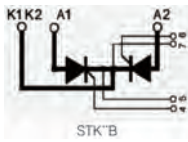
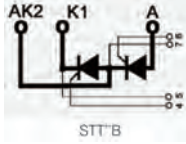


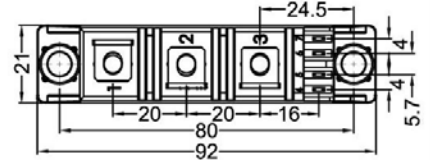
# STT49GKXXB

## Thyristor-Thyristor Modules



Type	V <sub>RSM</sub> V <sub>DSM</sub> V	V <sub>RRM</sub> V <sub>DRM</sub> V
STT49GK08B	900	800
STT49GK12B	1300	1200
STT49GK14B	1500	1400
STT49GK16B	1700	1600
STT49GK18B	1900	1800

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>TRMS</sub> , I <sub>FRMS</sub> I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> T <sub>C</sub> =85°C; 180° sine	76 49	A
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> =45°C V <sub>R</sub> =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	1150 1230 1000 1070	A
∫i <sup>2</sup> dt	T <sub>VJ</sub> =45°C V <sub>R</sub> =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	6600 6280 5000 4750	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> f=50Hz, t <sub>p</sub> =200us V <sub>D</sub> =2/3V <sub>DRM</sub> I <sub>G</sub> =0.45A di <sub>G</sub> /dt=0.45A/us repetitive, I <sub>T</sub> =150A non repetitive, I <sub>T</sub> =I <sub>TAVM</sub>	150 500	A/us
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> ; R <sub>GK</sub> =∞; method 1 (linear voltage rise) V <sub>DR</sub> =2/3V <sub>DRM</sub>	1000	V/us
P <sub>GM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> I <sub>T</sub> =I <sub>TAVM</sub> t <sub>p</sub> =30us t <sub>p</sub> =300us	10 5	W
P <sub>GAV</sub>		0.5	W
V <sub>RGM</sub>		10	V
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-40...+125 125 -40...+125	°C
V <sub>ISOL</sub>	50/60Hz, RMS I <sub>ISOL</sub> ≤1mA t=1min t=1s	3000 3600	V~
M <sub>d</sub>	Mounting torque (M5) Terminal connection torque (M5)	2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in.
Weight	Typical	110	g



# STT49GKXXB

## Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
$I_{RRM}, I_{DRM}$	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	5	mA
$V_{TM}$	$I_{TM}=150A; T_{VJ}=25^{\circ}C$	1.65	V
$V_{TO}$	For power-loss calculations only ( $T_{VJ}=125^{\circ}C$ )	0.85	V
$r_T$		5.3	$m\Omega$
$V_{GT}$	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
$I_{GT}$	$V_D=6V; T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
$V_{GD}$	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.2	V
$I_{GD}$		10	mA
$I_L$	$T_{VJ}=25^{\circ}C; t_p=10\mu s; V_D=6V$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	450	mA
$I_H$	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	200	mA
$t_{gd}$	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	$\mu s$
$t_q$	$T_{VJ}=T_{VJM}; I_T=120A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$ typ.	150	$\mu s$
$Q_S$	$T_{VJ}=T_{VJM}; I_T, I_F=50A; -di/dt=0.64A/\mu s$	90	$\mu C$
$I_{RM}$		11	A
$R_{thJC}$	per thyristor/diode; DC current per module	0.53 0.265	K/W
$R_{thJK}$	per thyristor/diode; DC current per module	0.73 0.365	K/W
$d_s$	Creeping distance on surface	12.7	mm
$d_A$	Strike distance through air	9.6	mm
$a$	Maximum allowable acceleration	50	$m/s^2$

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Glass passivated chips
- \* Isolation voltage 3600 V~
- \* UL file NO.E310749
- \* RoHS compliant

### APPLICATIONS

- \* DC motor control
- \* Softstart AC motor controller
- \* Light, heat and temperature control

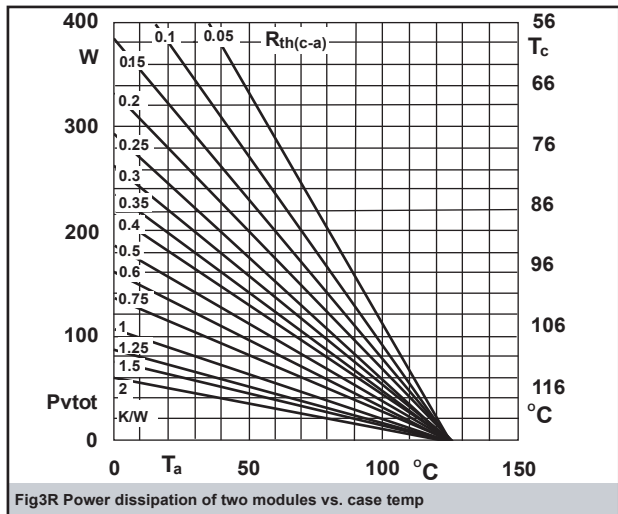
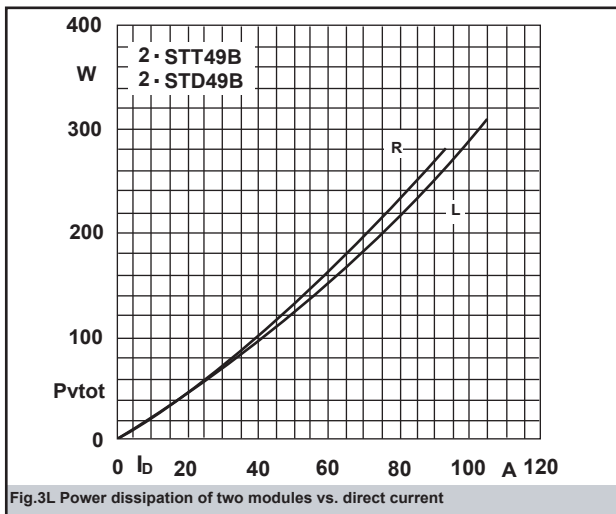
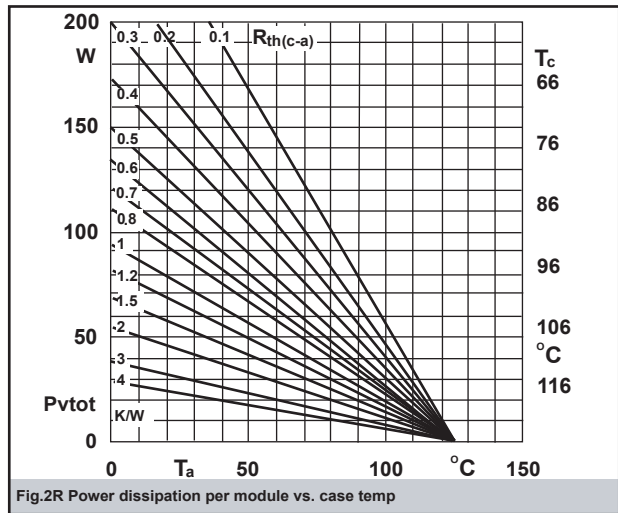
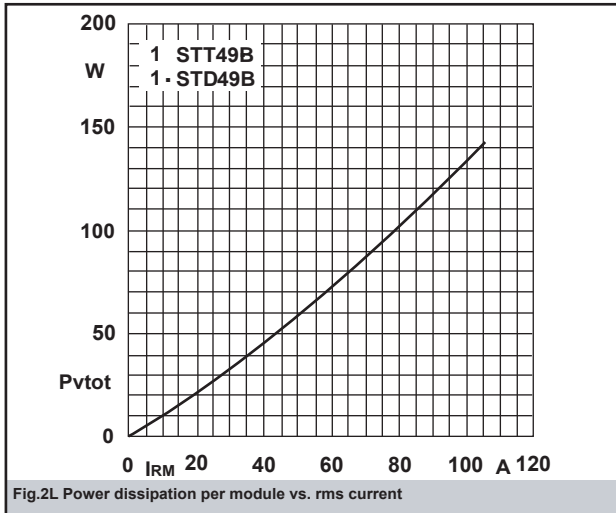
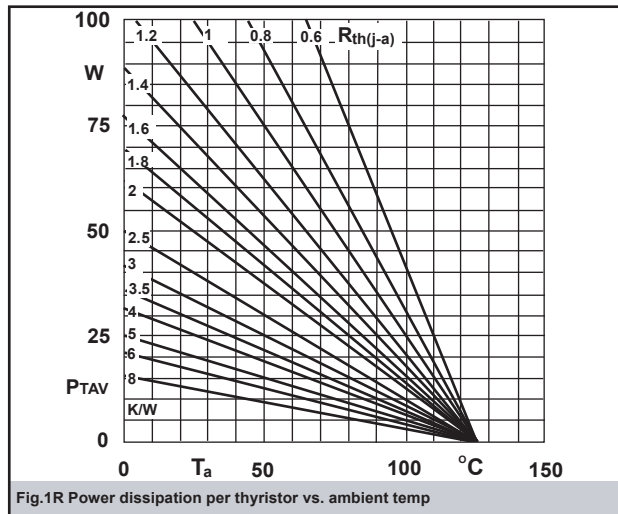
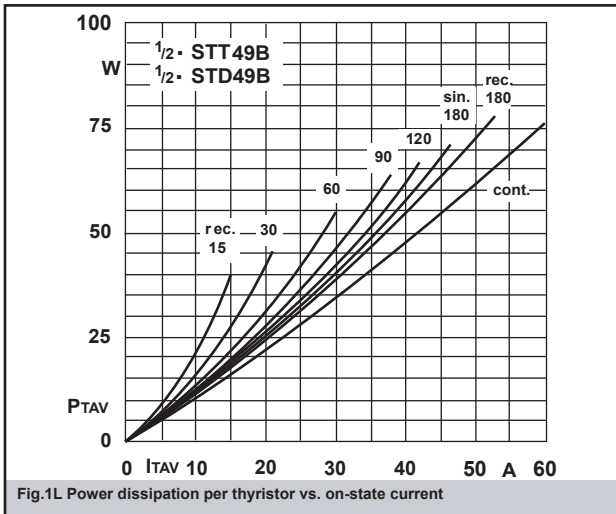
### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting with two screws
- \* Improved temperature and power cycling
- \* Reduced protection circuits



# STT49GKXXB

## Thyristor-Thyristor Modules



# STT49GKXXB

## Thyristor-Thyristor Modules

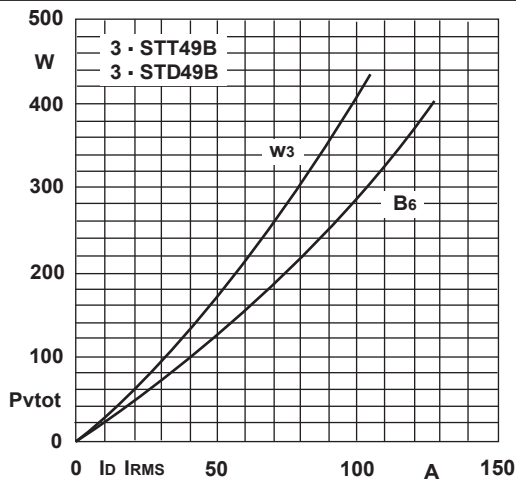


Fig.4L Power dissipation of three modules vs. direct and rms current

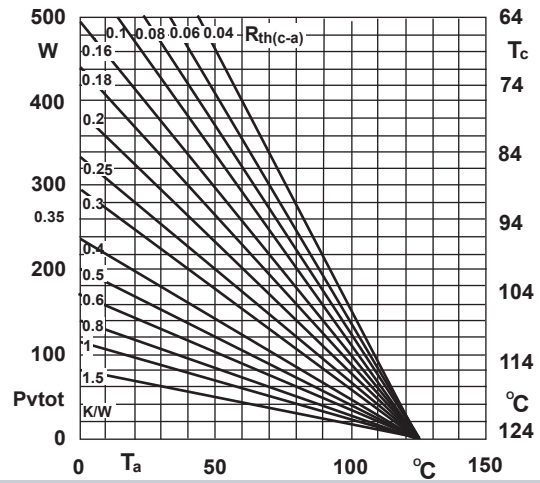


Fig.4R Power dissipation of three modules vs. case temp

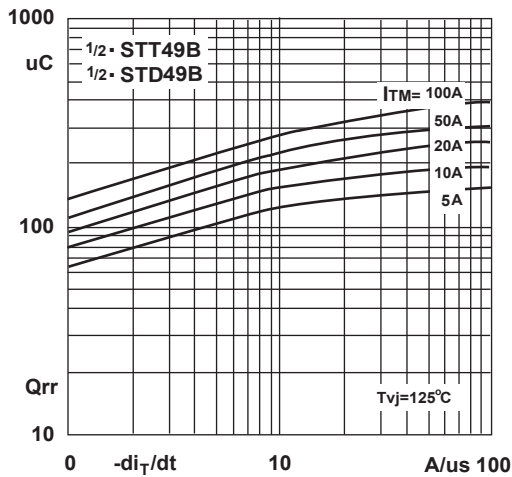


Fig.5 Recovered charge vs. current decrease

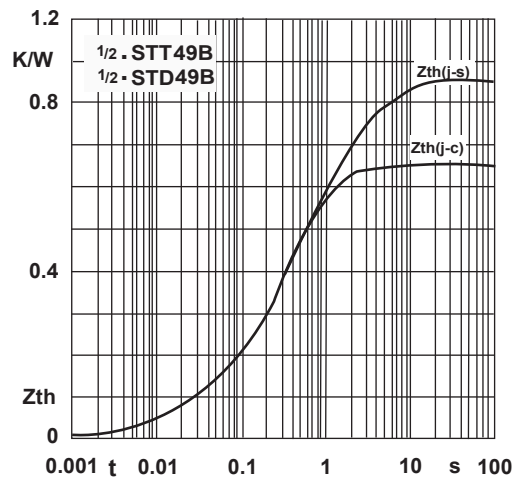


Fig.6 Transient thermal impedance vs. time

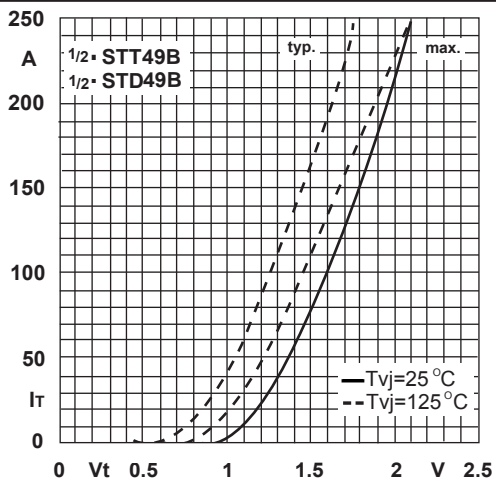


Fig.7 On-state characteristics

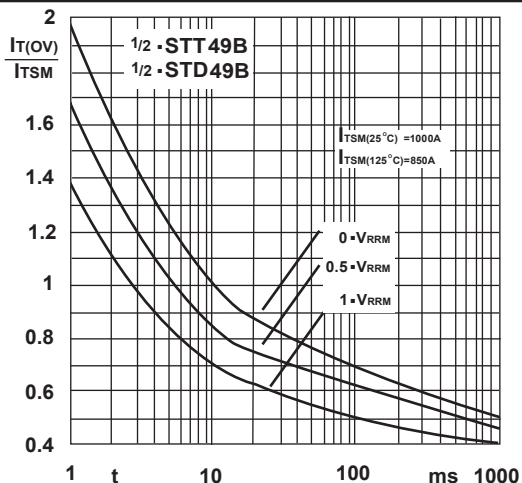


Fig.8 Surge overload current vs. time

**Sirectifier**<sup>®</sup>